

Mechanism of sign inversion of spontaneous polarization in ferroelectric SmC* liquid crystalsYoshitaka Mieda,^{1,*} Hajime Hoshi,¹ Yoichi Takanishi,¹ Hideo Takezoe,¹ and Boštjan Žekš²¹*Department of Organic and Polymeric Materials, Graduate School of Science and Engineering, Tokyo Institute of Technology, O-okayama, Meguro-ku, Tokyo 152-8552, Japan*²*Institute of Biophysics, Medical Faculty, Lipičeva 2, 1105 Ljubljana, Slovenia*

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The ferroelectric liquid crystal FLC-117, which is known to exhibit at a certain temperature the sign inversion of spontaneous polarization P_s , is studied under an electric field. From the analysis of the electro-optic response and the direct texture observations, it is concluded that the inversion temperature of P_s has the applied voltage dependence. To interpret our experimental result, we introduce a coupling term between the molecular dipole moments and the magnitude of the applied electric fields to the asymmetric rotational potential about the molecular long axis. The simulated results using this potential are in accordance with our experimental result.

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I. INTRODUCTION

The local ferroelectricity that characterizes the chiral smectic-C (SmC*) liquid crystal is due to the cooperative hindered rotation about the molecular long axis of the constituent molecules. In 1973, McMillan proposed a simple physical picture of the smectic-C (SmC) phase; the molecules rotate freely about their long axis in the smectic-A (SmA) phase and this rotation is partially frozen out in the SmC phase [1]. If McMillan's idea is correct, the SmC* phase ought to have a spontaneous polarization P_s along the local C_2 axis. In 1975, Meyer *et al.* realized this and proved it experimentally in the SmC* phase of DOBAMBC [2,3]. Since then, as is well known, various ferroelectric liquid crystalline materials have been synthesized and the physical properties of the ferroelectric liquid crystals (FLCs) have been investigated.

One of the most important findings in FLCs is the sign inversion phenomenon of P_s by the temperature change. In the past, the sign of P_s had been thought as the characteristic of the materials by nature. In 1986, however, two groups independently reported a new class of ferroelectric liquid crystals showing P_s sign inversion [4–6]. Since then, the P_s sign inversion phenomenon has been observed in various systems: single-component substances [4,6,7], two-component mixtures [8–10], and polymer systems [11].

Recently, we performed a detailed texture observation in a single-component material FLC-117 (Chisso) near the P_s inversion temperature T_{inv} and found that T_{inv} depends on the applied voltage. Although the same kind of phenomenon was suggested to occur by Glass *et al.* in the measurement of the pyroelectricity for the ferroelectric liquid crystal S-2-methylbutyl-4-*n*-decanoyloxybiphenyl-4'-carboxylate [12], they did not mention it clearly, so that this is essentially the first report of the phenomenon. Moreover, little is known about the texture near T_{inv} . The aim of this paper is to show this experimental result unambiguously and to interpret this

phenomenon using a microscopic model.

In the past, the P_s inversion phenomenon has been interpreted by various microscopic models [5,13,14]. Among them, one of the most well-known models is the dipolar-quadrupolar coupling model [14–17]. Based on Landau's theory for the SmA-SmC* phase transition, the first mathematical treatment of this model was given by Žekš *et al.* in 1988 [18]. In 1993, Meister and Stegemeyer extended this model to treat P_s sign inversion [14]; they assumed the sign inversion occurs due to the competition between the polar and the quadrupolar orders for the single-particle rotational potential about the molecular long axis. In this paper, we introduce a coupling term between a molecular dipole moment and the magnitude of an applied electric field to the rotational potential and simulate the P_s sign inversion phenomenon under the electric field.

The paper is organized as follows. In Sec. II we will show the experimental results. In Sec. III, to compare with the experimental results, we will define the rotational potential under an electric field, and calculate the numerical solution.

II. EXPERIMENT

FLC-117, which is known to show the P_s sign inversion, was used in this study [7]. Figure 1 shows the chemical structure and the phase sequence of this single-component material. The glass substrates with patterned indium tin oxide electrodes were washed by acetone, spin coated with polyimide, and rubbed unidirectionally. The two substrates were placed together with 2- μ m polyethylenterephthalate sheet spacers. FLC-117 was introduced into the cell by capillary suction in the isotropic phase. By cooling down from

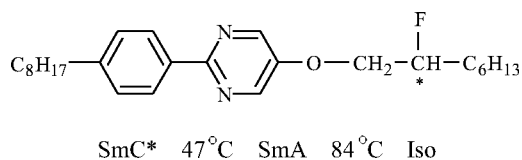


FIG. 1. The chemical structure and the phase sequence of FLC-117.

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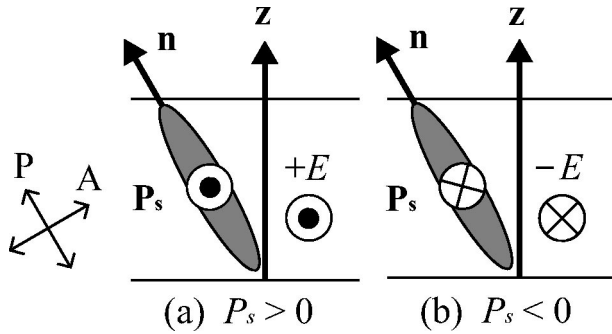


FIG. 2. The sign definition of the P_s . The circle with dot and the circle with cross represent the up and down directions with respect to the paper surface, respectively. E represents the magnitude of the electric field. P and A represent the polarizer and analyzer, respectively.

the isotropic phase to the SmA phase, a single domain with homogeneous alignment was obtained. The SmC* phase was obtained by the cooling process from the SmA phase. In the SmC* phase under zero electric field, surface stabilized ferroelectric liquid crystal bistable domains [19] were realized, i.e., the uniform textures remain stable after turning off the field (memory effect).

According to convention [20], P_s was defined by

$$\mathbf{P}_s = P_s \frac{\mathbf{z} \times \mathbf{n}}{|\mathbf{z} \times \mathbf{n}|}, \quad (1)$$

where \mathbf{P}_s is the local polarization vector, \mathbf{z} is the layer normal vector, and \mathbf{n} is the director. The definition of the sign of P_s is illustrated in Fig. 2. The magnitude of P_s was determined by the switching-current measurements [21] on applying a rectangular wave voltage (40 V, 30 Hz). The sign of P_s was determined by the tilt direction with respect to the layer normal under the dc electric field using a polarizing microscope. In Fig. 3, we show the temperature dependence of P_s and magnitude of the tilt angle θ . It is found that the P_s sign inversion occurs between 37 °C and 38.5 °C, which agrees with the previous result [7]. However, since P_s is very

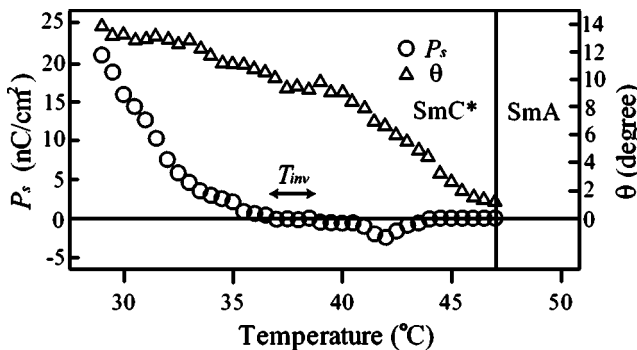


FIG. 3. The temperature dependence of P_s and the magnitude of θ for FLC-117 in a 2- μm cell. Circles and triangles represent P_s and θ , respectively. P_s sign inversion occurs between 37 °C and 38.5 °C.

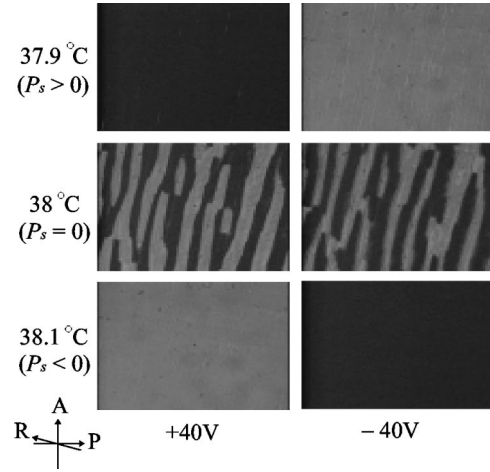


FIG. 4. The microphotographs of a 2- μm -thick FLC-117 sample cell between crossed polarizers. P , A , and R represent polarizer, analyzer, and rubbing directions, respectively. At 37.9 °C and at 38.1 °C, P_s signs are positive and negative, respectively. At 38 °C, both dark and bright views coexist, and the bistable domains show no response to the field, indicating that P_s is zero and $T_{inv} = 38$ °C.

small near the inversion point, the precise value of T_{inv} is not easy to be determined only by the switching current measurement.

The P_s inversion process could be directly observed by using a polarizing microscope. Texture observation was made under a rectangular wave of 0.05 Hz with 40 V. The polarizer and analyzer were set to be crossed and arranged to give a dark view for the situation of Figs. 2(a) and 2(b); positive and negative voltages give a dark view for $P_s > 0$ and $P_s < 0$, respectively.

Figure 4 shows microphotographs near T_{inv} . At 37.9 °C, P_s is positive, since the situation given by Fig. 2(a) is obtained. At 38.1 °C, on the contrary, the behavior is opposite to that for 37.9 °C; P_s is negative. At 38 °C, both dark and bright views coexist with the tilt angle 9.5°, and the bistable domains do not respond to the field, indicating that P_s is zero. Namely, T_{inv} is 38 °C. In this way, from the direct texture observation, the exact inversion point could be determined.

Moreover, we measured the electro-optic response by applying a triangular wave field near the inversion temperature. The frequency and the amplitude of the applied triangular voltage were 0.1 Hz and 80 V, respectively. At 37 °C, bistable switching was observed, as shown in Fig. 5(a). Bistable switching was also observed at 39 °C, but the phase is opposite to that at 37 °C, as shown in Fig. 5(c). These results indicate that the signs of P_s are opposite at 37 °C and 39 °C. Stars and circles in Fig. 5 specify the response by positive and negative P_s , respectively. An interesting electrooptic response was observed at 38 °C [Fig. 5(b)]. At a voltage higher than 40 V, the behavior is the same as that at 37 °C, as marked by stars. Therefore, P_s is positive above 40 V. On the other hand, the response below 40 V shows that P_s is negative.

To investigate the unusual switching in Fig. 5(b), at

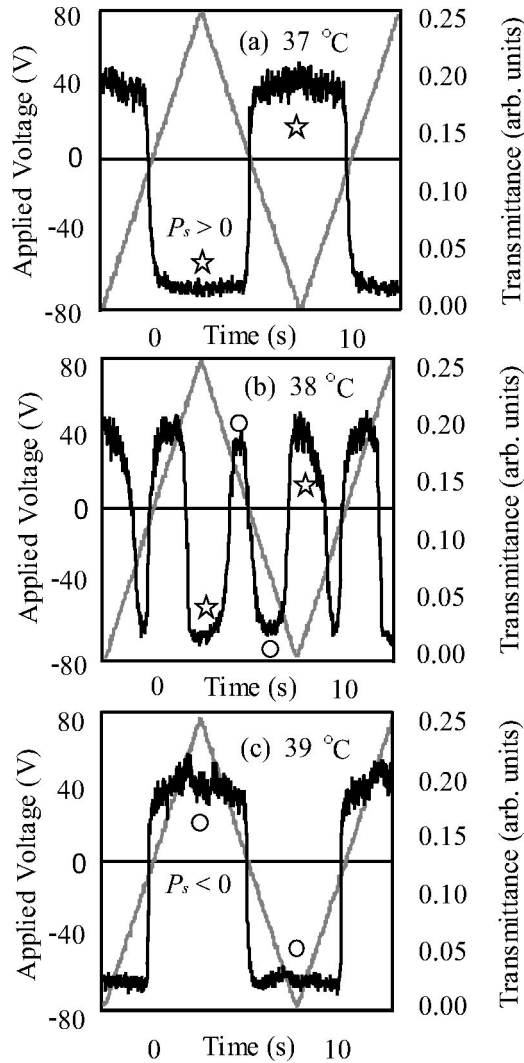


FIG. 5. The optical response for a triangular wave of 0.1 Hz with 80 V at (a) 37 °C, (b) 38 °C, and (c) 39 °C. Stars and circles specify the optical response for $P_s > 0$ and $P_s < 0$, respectively. At 38 °C, P_s is positive at a high voltage region and negative at a low voltage region.

38 °C we applied a rectangular wave field of 0.05 Hz with different voltages (20 V, 40 V, 80 V) and texture observation was executed. For 40 V, bistable domains show no switching [Fig. 6(b)]. For 20 V, switching is observed, as shown in Fig. 6(a), which indicates that P_s is negative. On the other hand, for 80 V, the switching indicating positive P_s was observed [Fig. 6(c)]. Of course, these results are consistent with the result of the electro-optic response in Fig. 5(b). But these results suggest the possibility that T_{inv} has an applied voltage dependence, $T_{inv} \neq 38$ °C under 20 V and 80 V.

The shift of T_{inv} under 20 V and 80 V was confirmed by the same direct texture observation made under 40 V. The results are given in Table I. This table shows that T_{inv} increases with the increase of the applied voltage strength.

It is important to emphasize that the thermal effect of the voltage does not lead to this behavior. Namely, if higher voltage causes a higher temperature of the cell, the observed T_{inv} should shift toward a lower temperature. This is just

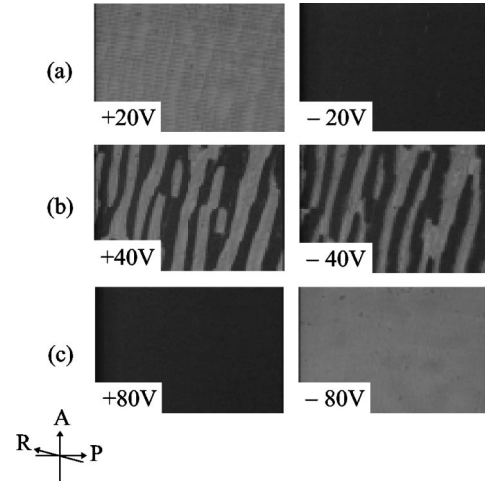


FIG. 6. The applied voltage dependence of the texture at 38 °C. P , A , and R represent polarizer, analyzer and rubbing directions, respectively. The voltage sequence is (a) 20 V, (b) 40 V, and (c) 80 V.

opposite to our experimental results. In this way, we could unambiguously conclude that T_{inv} for FLC-117 has an applied voltage dependence.

III. DISCUSSION

A. A molecular model for P_s sign inversion

P_s originates from the hindered rotational motion about the long molecular axis. To describe the model, right-handed rectangular laboratory coordinates (x, y, z) and right-handed rectangular molecular coordinates (ξ, η, ζ) are introduced (Fig. 7), where the z axis is the smectic layer normal, y is the C_2 axis, ζ is the molecular long axis, and ξ is the axis of the electric dipole moment projected on the ξ - η plane. Moreover, the angles (θ, ψ) are introduced to describe the relation between (x, y, z) and (ξ, η, ζ) , where θ is the tilt angle from the z axis, and ψ is the rotational angle about the ζ axis (we define the counterclockwise rotation to be positive). Now we assume that molecular energy is determined by a molecular potential $V_0(\psi)$. The potential under an electric field is given by

$$V(\psi) = V_0(\psi) - \mu_{\text{eff}} E. \quad (2)$$

Here, E and μ_{eff} are the magnitudes of the applied electric field and the effective molecular dipole moment for the y direction, respectively. Generally, the molecular distribution function $f(\psi)$ is given by

TABLE I. The applied voltage dependence of the P_s inversion temperature T_{inv} determined by the direct texture observation.

Applied voltage (V)	P_s inversion temperature (°C)
20	37.9
40	38
80	38.1

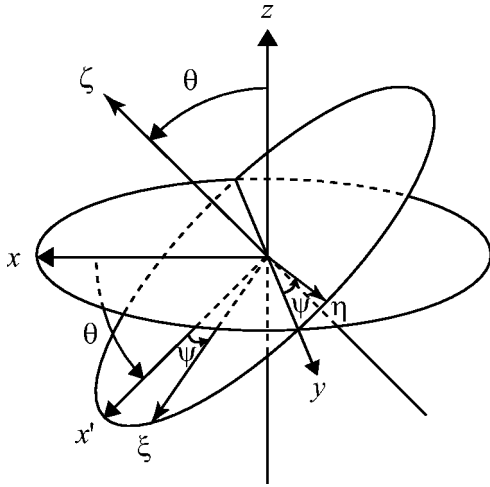


FIG. 7. The definition of laboratory coordinates (x, y, z) , molecular coordinates (ξ, η, ζ) , and the angles (θ, ψ) . x' axis represents the ξ axis at $\psi=0$.

$$f(\psi) = \frac{1}{Z} \exp\left(\frac{-V(\psi)}{k_B T}\right), \quad (3)$$

where Z is the partition function, k_B is the Boltzmann constant, and T is the temperature. Using this distribution function, P_s is given by

$$P_s = N \langle \mu_{\text{eff}} \rangle = N \mu_\xi \langle \sin \psi \rangle, \quad (4)$$

where N is the number density of the molecule, $\langle \dots \rangle$ represents the ensemble average, and $\mu_\xi (>0)$ is the ξ component of the molecular dipole moment. The sign of P_s is determined by $\langle \sin \psi \rangle$. Here let us consider the mechanism of P_s sign inversion. Suppose that $V_0(\psi)$ has a symmetric form at $\psi = \psi_0 (>0)$ as shown in Fig. 8(a), namely $V_0(\psi_0 - \psi) = V_0(\psi_0 + \psi)$; such a symmetric potential was actually adopted as the binding site model in Ref. [22]. However, the sign inversion is impossible in this potential because the population for $\psi > 0$ is more than that for $\psi < 0$ for all temperatures. On the other hand, if molecular chirality is very strong and $V_0(\psi)$ has the asymmetric form as shown in Fig. 8(b), sign inversion is possible. In this case, because of the asymmetry of the potential, at low temperature, $\psi > 0$ has a large population, while at high temperature, $\psi < 0$ is more populated.

B. Numerical calculation using an asymmetric potential

To calculate the numerical solution of the electric field effect on T_{inv} , we consider a more realistic potential. In general, the potential should vanish at the SmA-SmC* transition point, because the molecules in the SmA phase rotate freely about molecular long axes. To consider this effect, we introduce the θ dependent potential $V_0(\theta, \psi)$, where θ is the primary order parameter of the SmC* phase. For θ dependence, we assume the following form:

$$V_0(\theta, \psi) = (\theta + \theta^2 + \dots + \theta^n + \dots) V_0(\psi), \quad (5)$$

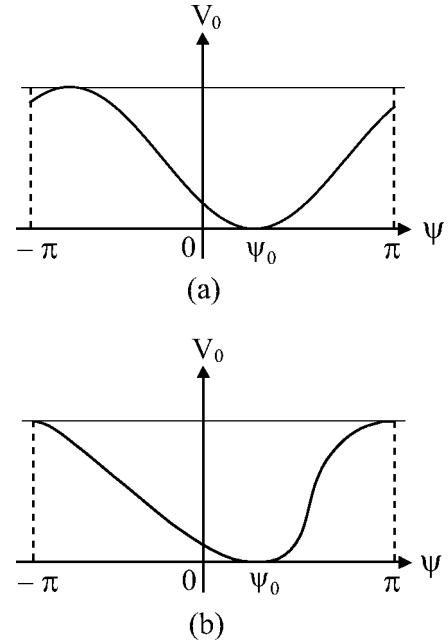


FIG. 8. (a) The symmetric rotational potential function. The ψ_0 represents the angle showing the potential minimum. (b) The asymmetric rotational potential function arising from the strong chirality. If the sign of the chirality is inverted, $V_0(\psi)$ is reversed with respect to the $\psi=0$. The ψ_0 locates in the positive ψ region in the present experimental condition as in the figure, hence $P_s > 0$ at low temperatures.

where the constant term is neglected, since only the relative value is important. Moreover, we expand $V_0(\psi)$ as a Fourier series:

$$V_0(\psi) = D_1 \cos(\psi - \omega_1) + D_2 \cos 2(\psi - \omega_2) + \dots + D_n \cos n(\psi - \omega_n) + \dots, \quad (6)$$

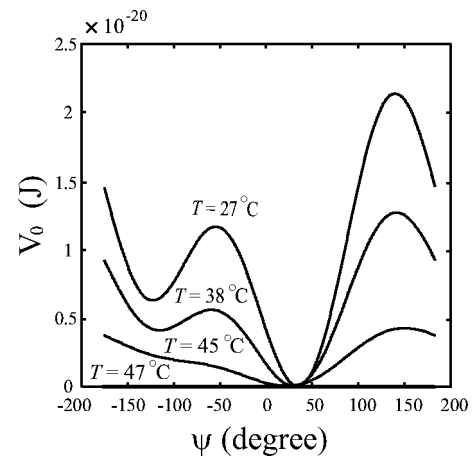


FIG. 9. The temperature dependence of the asymmetric potential function represented by the Fourier expansion. The parameters used for this calculation are $A = 4.07 \times 10^{-22}$, $B = 0.3 \times 10^{-22}$, $\omega_1 = -19^\circ$, $\omega_2 = 40.5^\circ$, and $\theta_0 = 3.25$. Temperature sequence is 27°C , 38°C , 45°C , and 47°C .

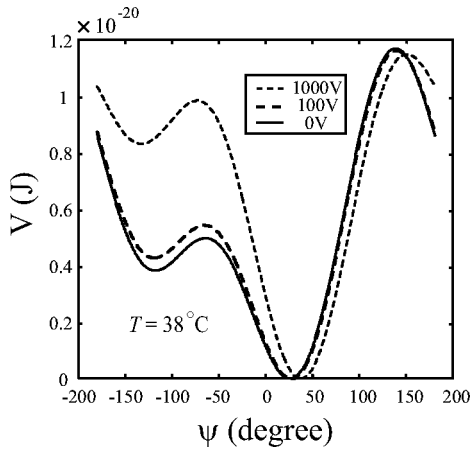


FIG. 10. The applied electric field dependence of the asymmetric rotational potential function. We assumed that the sample was introduced between two electrodes with a $2\text{-}\mu\text{m}$ gap. The sequence of the applied voltage is 0-V bias=0 V/cm, 100-V bias= 5×10^5 V/cm, and 1000-V bias= 5×10^6 V/cm. In this calculation, we put $\mu_\xi = 2$ D.

where D_n are the expansion coefficients and ω_n are the phases. In particular, we use the following potential

$$V_0(\theta, \psi) = -A\theta \cos(\psi - \omega_1) - B\theta^2 \cos 2(\psi - \omega_2), \quad (7)$$

where $A > 0$ and $B > 0$, which has been proposed by Žekš *et al.* [18]. This equation is the most simple potential satisfying the symmetry requirement $V_0(\theta, \psi) = V_0(-\theta, \psi + \pi)$. According to the Landau theory, the temperature dependence of θ is given by

$$\theta = \theta_0(T_c - T)^{0.5}, \quad (8)$$

where θ_0 is the proportional constant and T_c is the Curie temperature for the SmA-SmC* phase transition. Figure 9 shows the temperature dependence of $V_0(\psi)$. Above $T_c = 47^\circ\text{C}$, since the molecules rotate freely, the rotational potential vanishes. Under the electric field, the potential is given by Eq. (2). Figure 10 shows the electric field dependence of the potential function. It is found that the stronger the magnitude of the electric field is, the bigger the potential deviation is. Moreover, the molecular dipole moment under an electric field is obtained by using Eq. (4). Figure 11 shows the temperature and the applied electric field dependence of

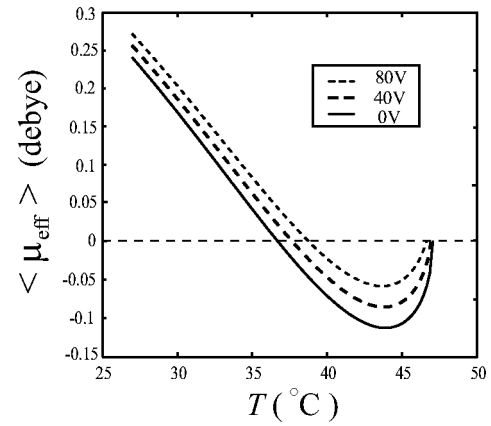


FIG. 11. The temperature and the applied electric field dependence of the average effective dipole moment. The sequence of the applied voltage is 0-V bias=0 V/cm, 40-V bias= 20×10^4 V/cm, and 80-V bias= 40×10^4 V/cm.

the average effective dipole moment. It is clearly found that P_s inversion has occurred. From this figure, it is also found that T_{inv} has the applied voltage dependence. Namely, when the applied voltage increases, T_{inv} also increases, being consistent with the present experiment.

IV. CONCLUSION

Under the electric fields, the ferroelectric liquid crystal FLC-117, which exhibits the P_s sign inversion phenomenon, was studied. From the analysis of the electro-optic response and the direct texture observations by using a polarizing microscope, it was confirmed that the inversion temperature T_{inv} of P_s increases with the increase of the applied voltage strength. To explain this applied voltage dependence of T_{inv} , we introduced a coupling term between a molecular dipole moment and the magnitude of an electric field applied to the asymmetric rotational potential about the molecular long axis. The numerical calculations using this potential were in accordance with our experimental results.

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